

TGD N-Channel Enhancement Mode Power MOSFET

**Description**

The TGD4009S uses advanced trench technology to provide excellent  $R_{DS(ON)}$  and low gate charge . The complementary MOSFETs may be used to form a level shifted high side switch, and for a host of other applications.

**General Features**

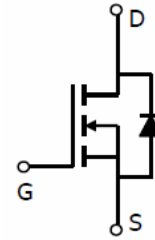
● **N-Channel**

$V_{DS} = 40V, I_D = 9A$

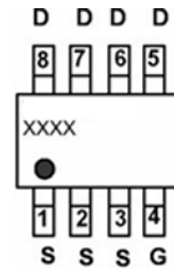
$R_{DS(ON)} < 16m\Omega @ V_{GS}=10V$

$R_{DS(ON)} < 24m\Omega @ V_{GS}=4.5V$

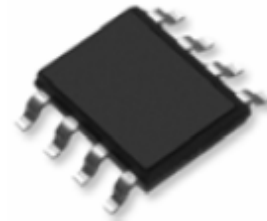
- High power and current handing capability
- Lead free product is acquired
- Surface mount package



Schematic diagram



pin assignment



SOP-8 top view

**Package Marking and Ordering Information**

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
TGD4009S	TGD4009S	SOP-8	Ø330mm	12mm	2500 units

**Absolute Maximum Ratings ( $T_C=25^{\circ}C$  unless otherwise noted)**

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	40	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous	$I_D$	9	A
Drain Current-Continuous( $T_C=100^{\circ}C$ )	$I_D(100^{\circ}C)$	6.4	A
Pulsed Drain Current	$I_{DM}$	40	A
Maximum Power Dissipation	$P_D$	2	W
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 150	$^{\circ}C$

**Thermal Characteristic**

Thermal Resistance, Junction-to-Ambient <sup>(Note 2)</sup>	$R_{\theta JA}$	62.5	$^{\circ}C/W$
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**N-CH Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)**

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	40	-	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =40V, V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	-	-	±100	nA
<b>On Characteristics (Note 3)</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	1	1.5	2.0	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =8A	-	12.9	16	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =4A	-	18.9	24	mΩ
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =5V, I <sub>D</sub> =8A	33	-	-	S
<b>Dynamic Characteristics (Note4)</b>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V, F=1.0MHz	-	964	-	PF
Output Capacitance	C <sub>oss</sub>		-	109	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>		-	96	-	PF
<b>Switching Characteristics (Note 4)</b>						
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =20V, R <sub>L</sub> =2.5Ω V <sub>GS</sub> =10V, R <sub>GEN</sub> =3Ω	-	5.5	-	nS
Turn-on Rise Time	t <sub>r</sub>		-	14	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>		-	24	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	12	-	nS
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =20V, I <sub>D</sub> =8A, V <sub>GS</sub> =10V	-	22.9	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	3.5	-	nC
Gate-Drain Charge	Q <sub>gd</sub>		-	5.3	-	nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =9A	-	0.8	1.2	V

N- Channel Typical Electrical and Thermal Characteristics (Curves)

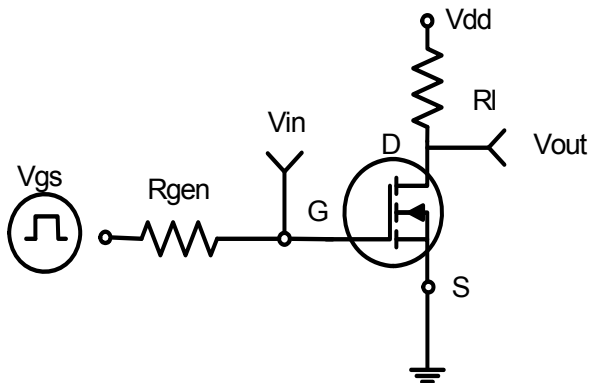


Figure 1: Switching Test Circuit

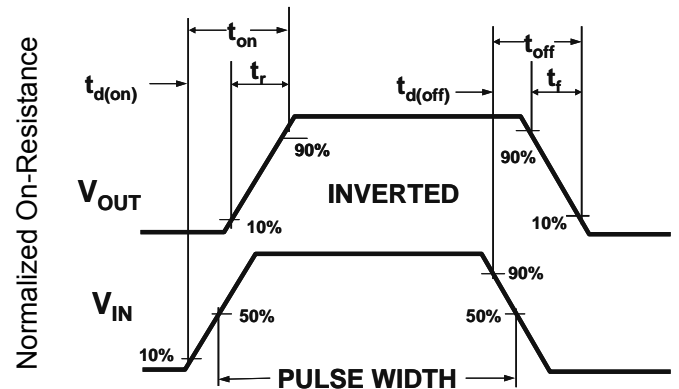


Figure 2: Switching Waveforms

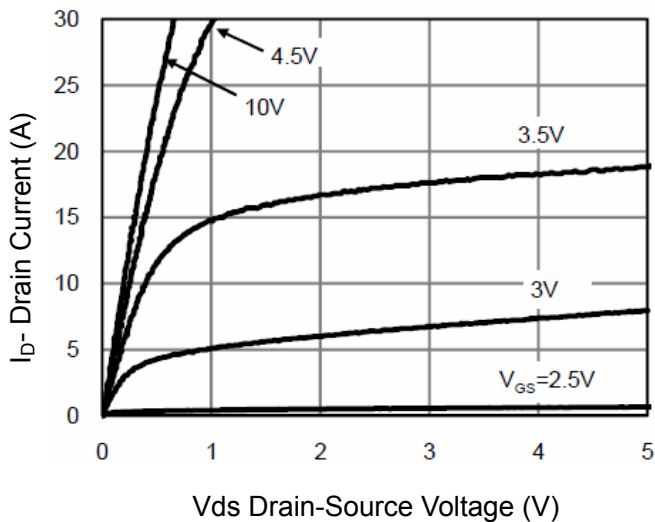


Figure 3 Output Characteristics

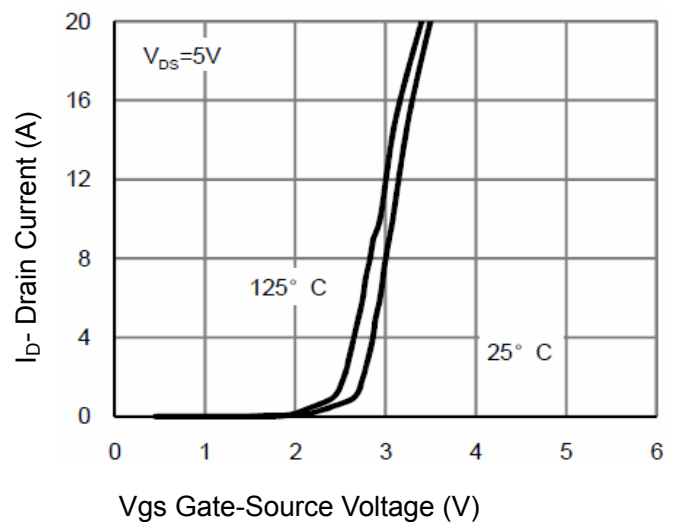


Figure 4 Transfer Characteristics

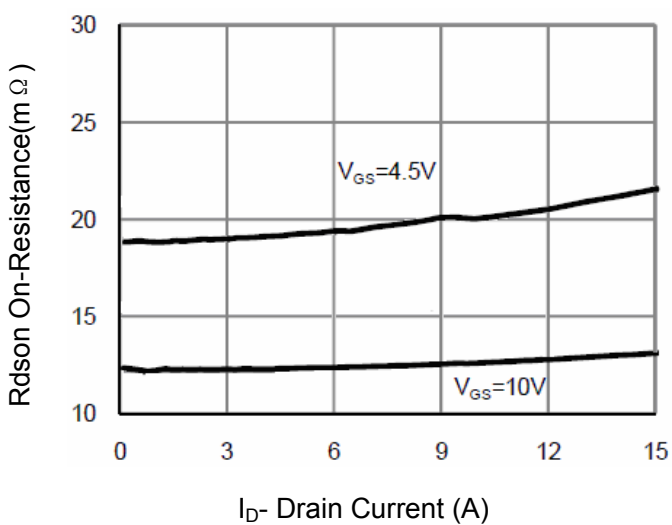


Figure 5 Drain-Source On-Resistance

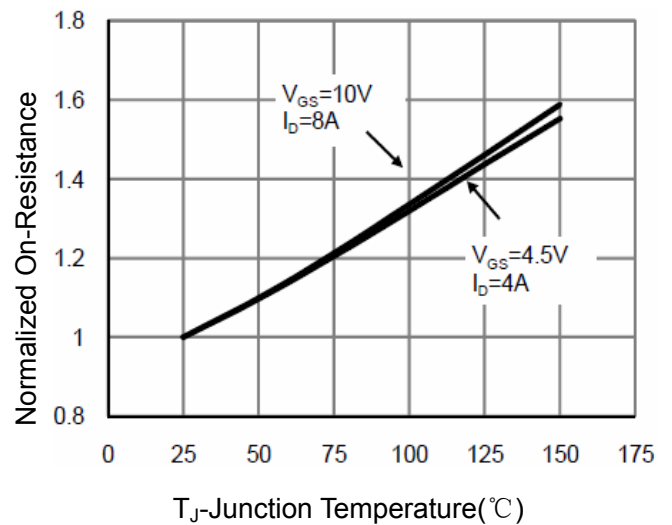
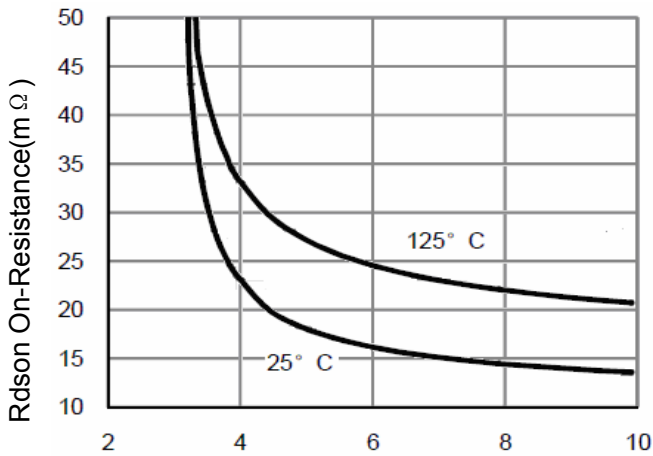
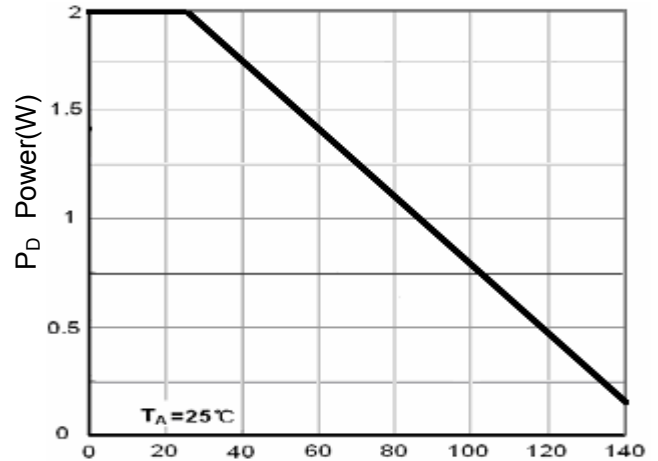


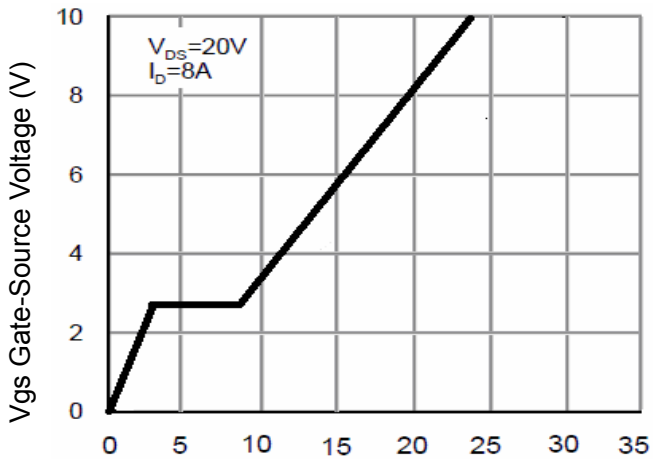
Figure 6 Drain-Source On-Resistance



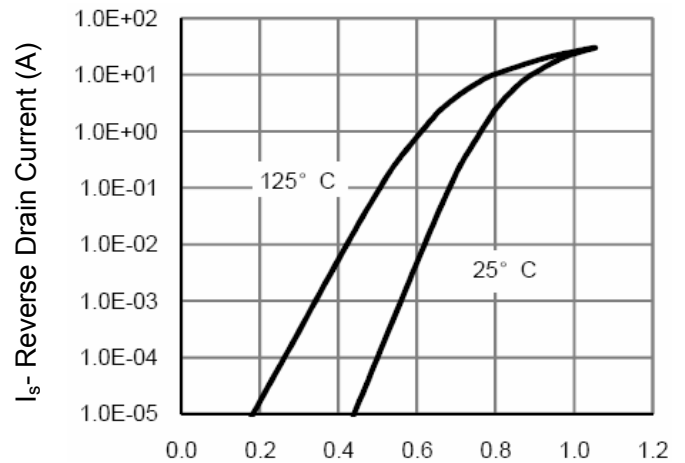
Vgs Gate-Source Voltage (V)  
**Figure 7 Rdson vs Vgs**



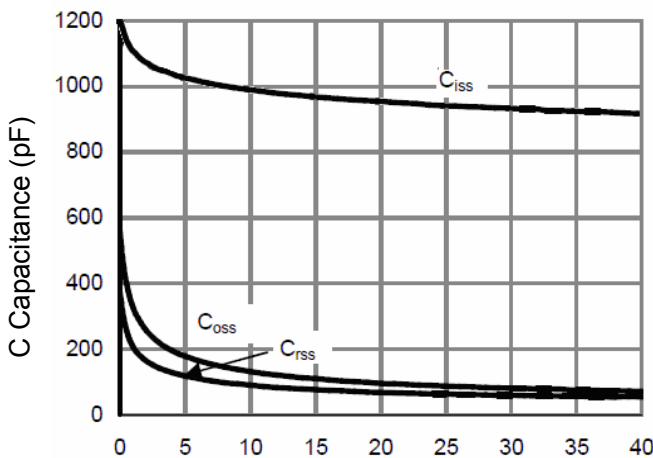
Tj Junction Temperature (°C)  
**Figure 8 Power Dissipation**



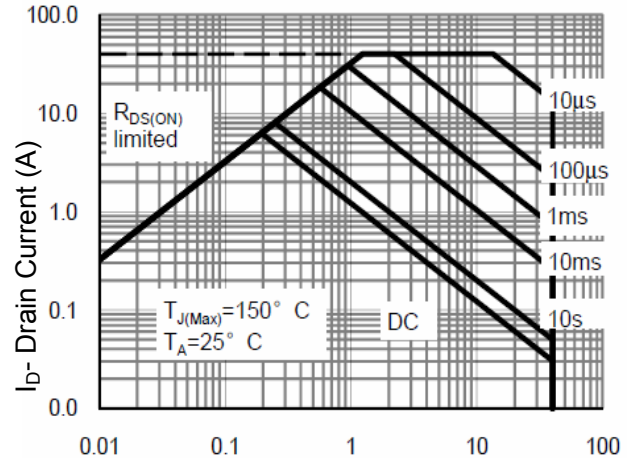
Qg Gate Charge (nC)  
**Figure 9 Gate Charge**



Vds Drain-Source Voltage (V)  
**Figure 10 Source- Drain Diode Forward**



Vds Drain-Source Voltage (V)  
**Figure 11 Capacitance vs Vds**



Vds Drain-Source Voltage (V)  
**Figure 12 Safe Operation Area**

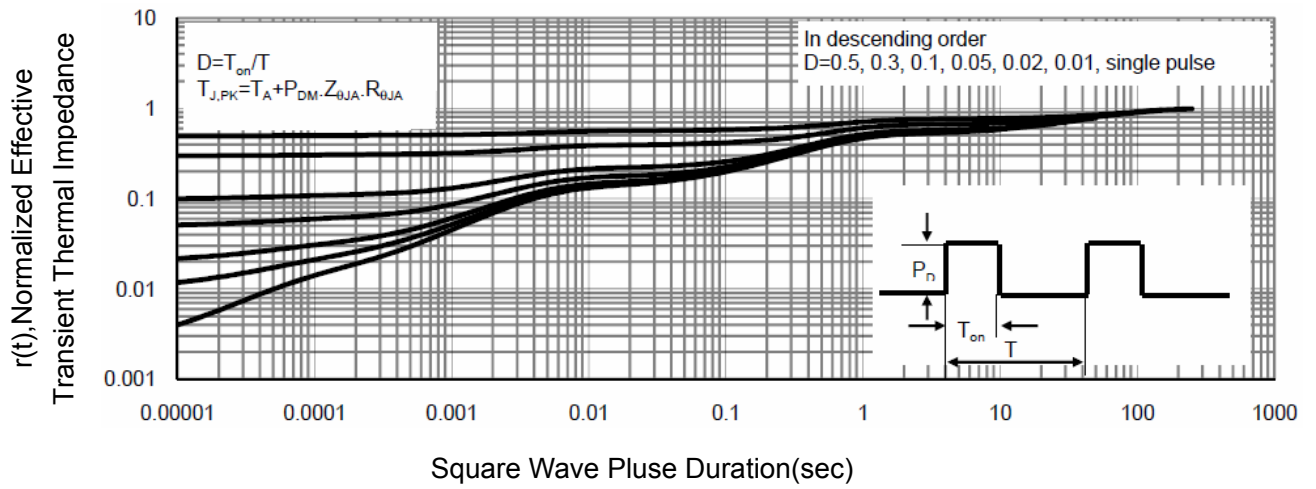
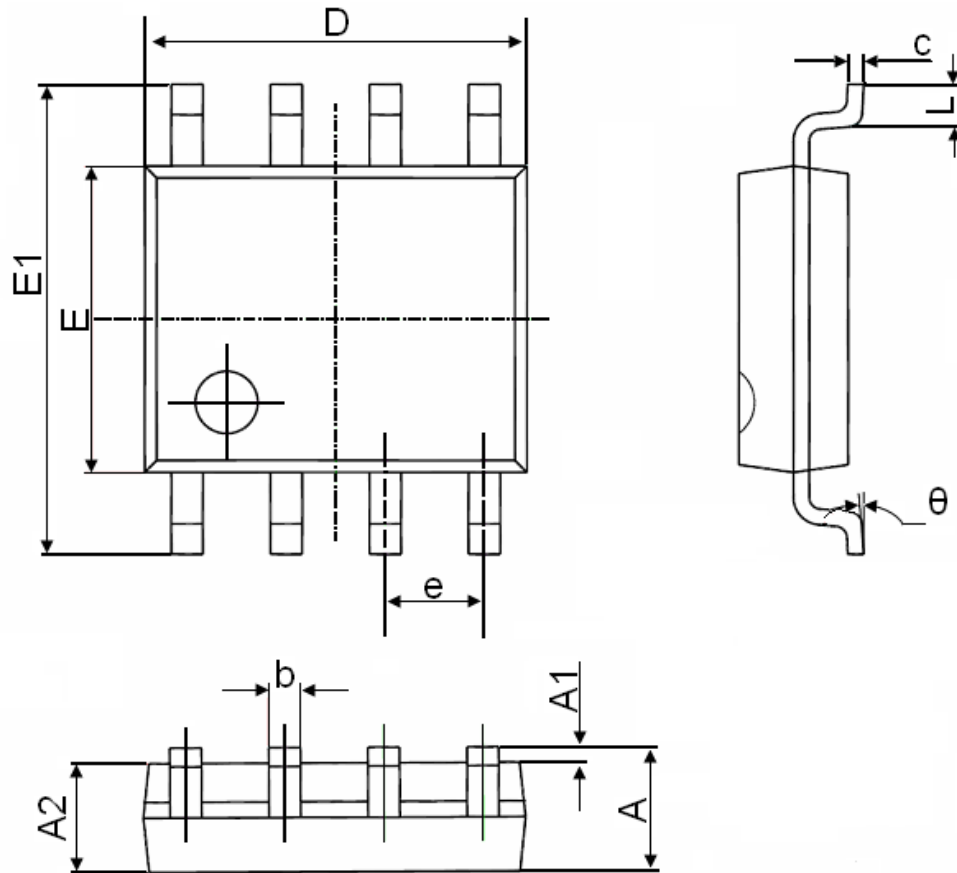


Figure 13 Normalized Maximum Transient Thermal Impedance

SOP-8 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
$\theta$	0°	8°	0°	8°